Safe Harbor Statement

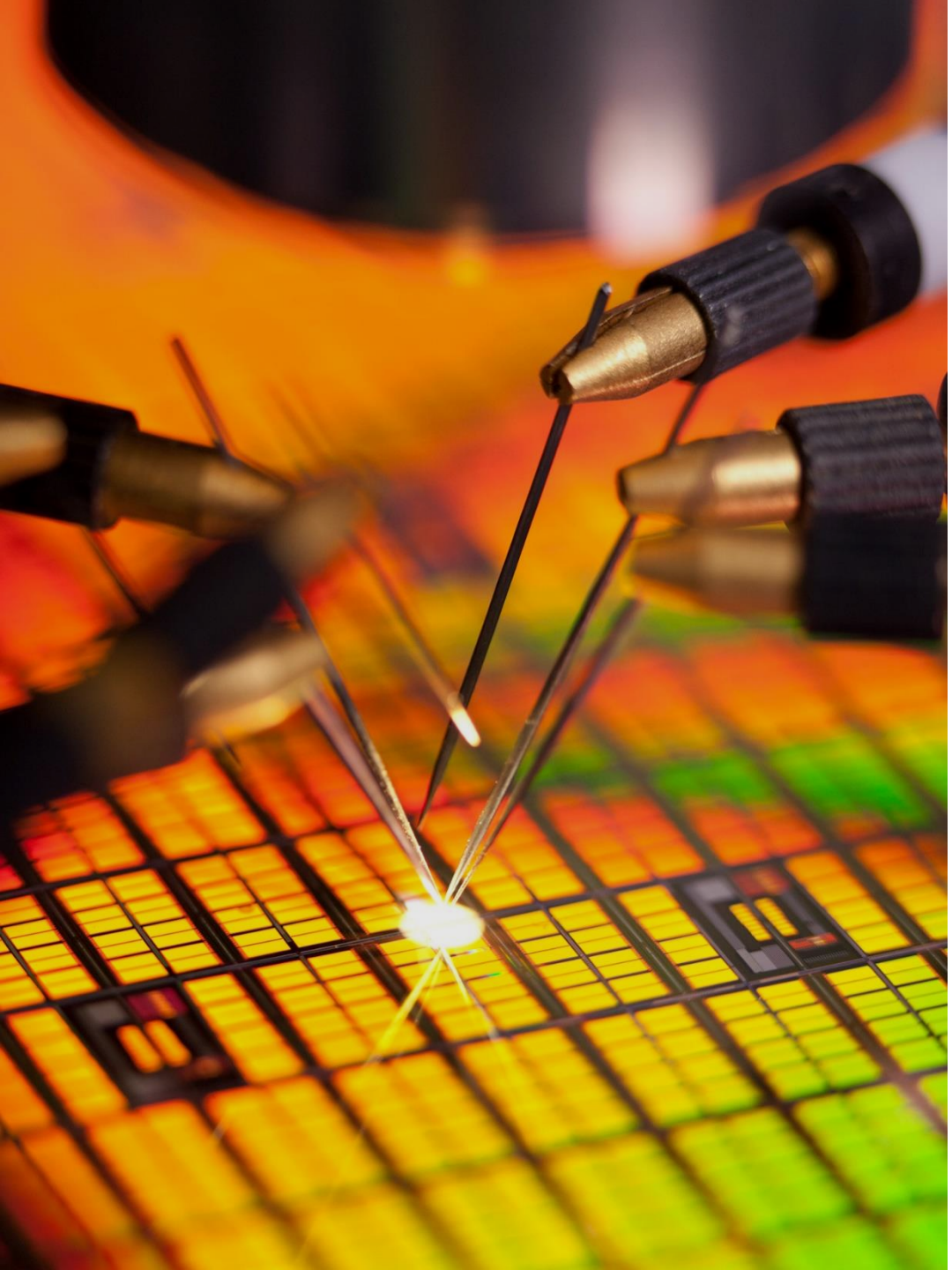
During the course of this meeting, we may make projections or other forward-looking statements regarding future events or the future financial performance of the Company and the industry. We wish to caution you that such statements are predictions and that actual events or results may differ materially. We refer you to the documents the Company files from time to time with the Securities and Exchange Commission, specifically the Company's most recent Form 10-K and Form 10-Q. These documents contain and identify important factors that could cause the actual results for the Company to differ materially from those contained in our projections or forward-looking statements. These certain factors can be found at http://www.micron.com/certainfactors. Although we believe that the expectations reflected in the forward-looking statements are reasonable, we cannot guarantee future results, levels of activity, performance or achievements. We are under no duty to update any of the forward-looking statements after the date of the presentation to conform these statements to actual results.

Accelerating Memory and Storage Innovation

Scott DeBoer, Executive Vice President

2019 Analyst & Investor Webcast | May 2019

Micron®



Agenda

- Team
- Core Technology
- Execution

Team

Core Technology

Execution

Industry's Best Talent

Getting Even Stronger

Team

Strong and Getting Stronger

Global talent fuels innovation

Top 50 on US Patent list

Forbes 2019 "The Best Employer for Diversity" list

New Talent

Attracting the World's Best

>50% of R&D new hires with MS, PhD

>60% technical with industry experience

Certified 2018 Great Place to Work

Pipeline

Advancing STEM Education

Advancing Curiosity grants

Promoting STEM education

Engaged with top global universities

Global Technology Development

Delivering World Leading Innovation and Execution

Core R&D
Idaho, U.S.

Accelerate Core Technology with Disruptive Innovation

DRAM
Japan

NAND
Singapore

3D XPoint™
Utah, U.S.

Packaging
Taiwan

Automotive
Virginia, U.S.

Strong Development Capability at Manufacturing Locations

Core Technology Delivering Across Spectrum of Customer Needs

Reliable High Bandwidth	Reliable High Performance	Light &Thin Low Power

Micron

Team

Core Technology

Execution

Core Technology

The Industry's Most Comprehensive Technology Portfolio

DRAM

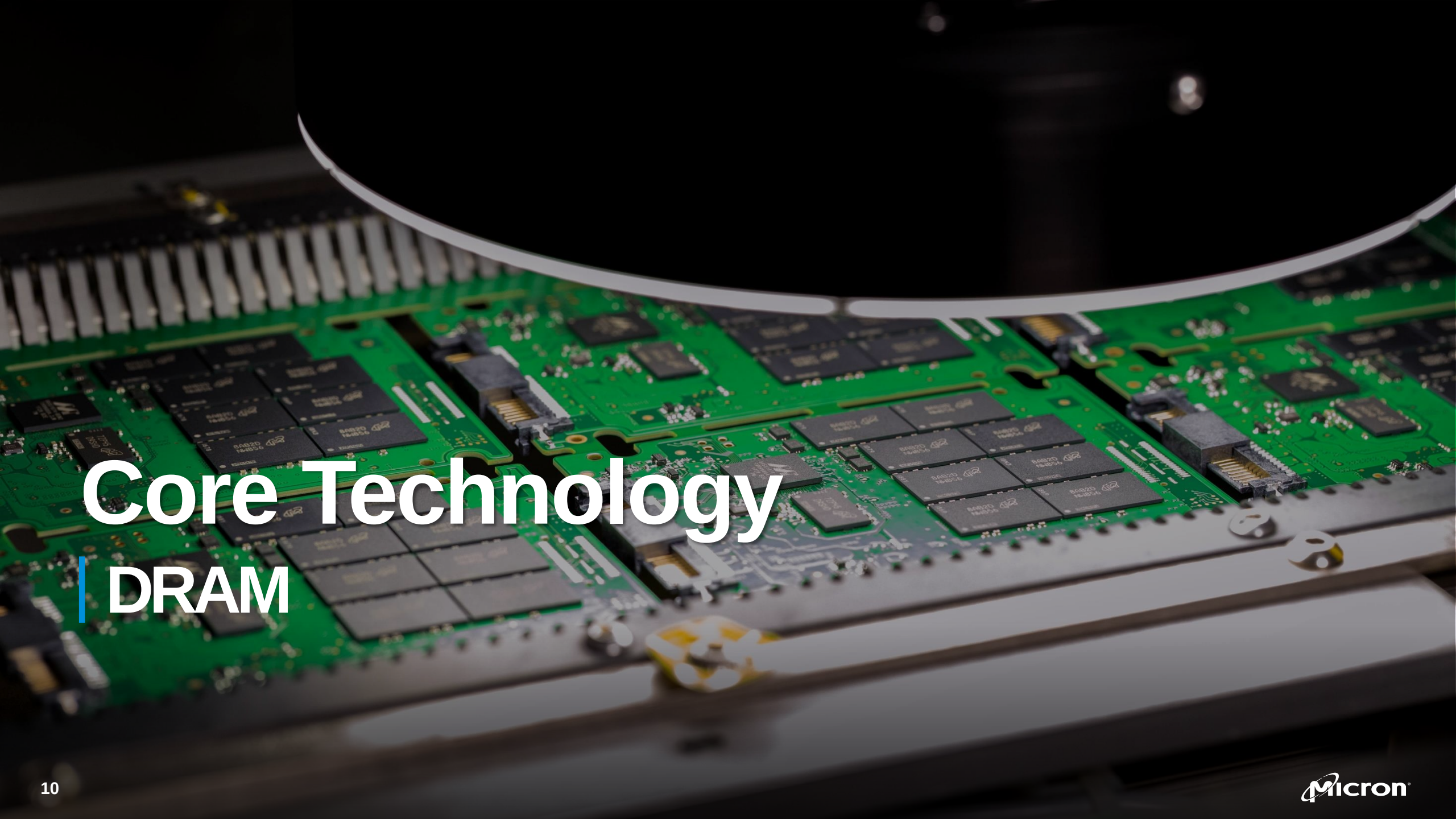
3D NAND

NOR

3D XPoint™

3D Packaging

Emerging Technologies



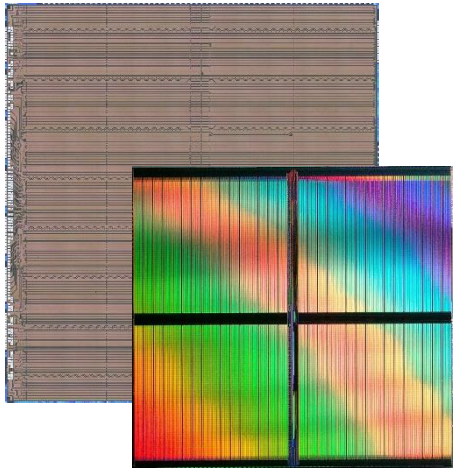
Core Technology

DRAM

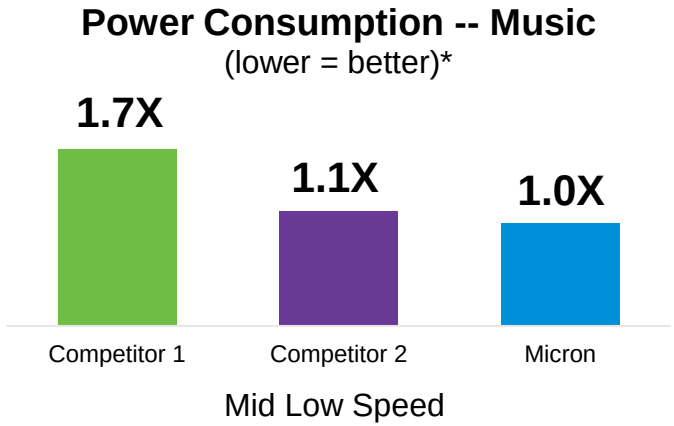
1Znm DRAM

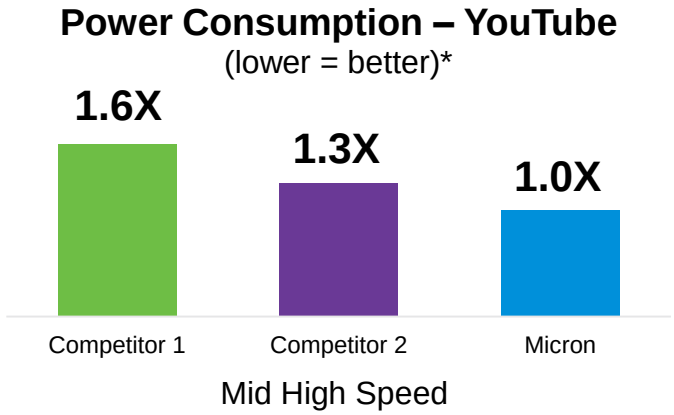
Continuing Rapid Improvement in Competitive Position

- Industry leading mobile 16Gb
- Rapid progress on 1Znm yield ramp
- Strengthening competitive position



1Znm DRAM: 16Gb LP-DDR4



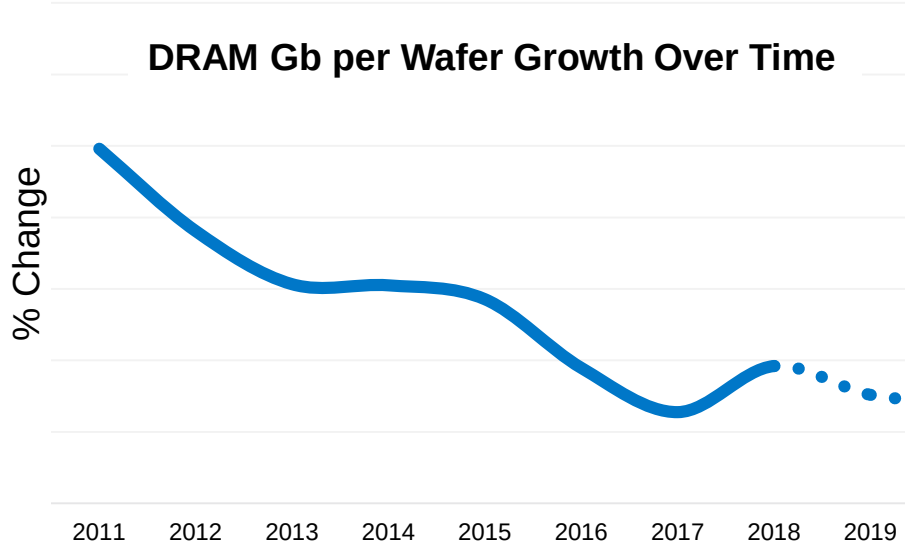


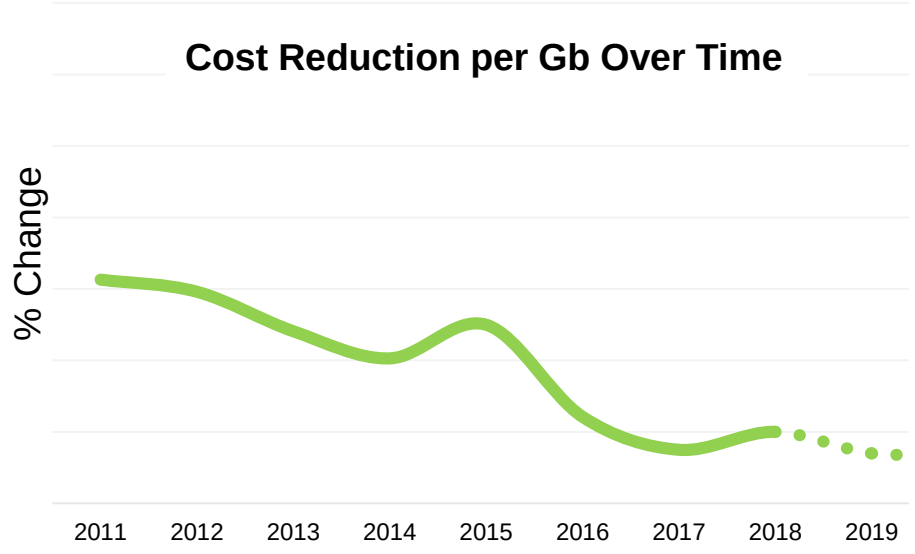
*Source: Micron – performance based on competitor samples and results may vary

DRAM Scaling Trends

DRAM Scaling Challenges Evident in Industry Trends

- Gb/Wafer increases significantly more difficult
- Cost of node transitions challenging ultimate benefits
- Capex Intensity continues to grow

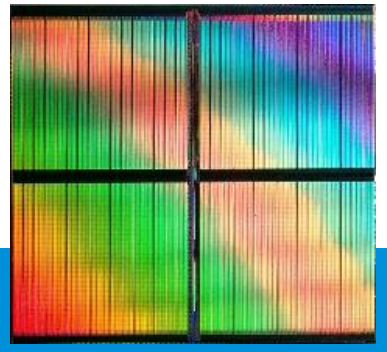




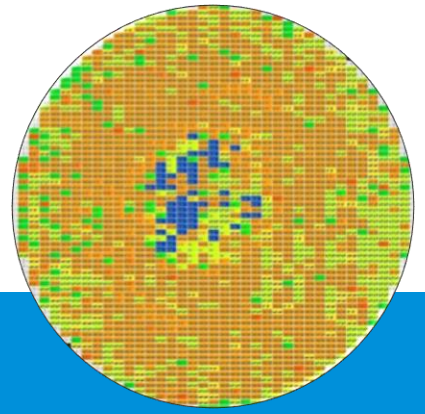
Source: Micron

DRAM Scaling: Driving Towards Technology Leadership

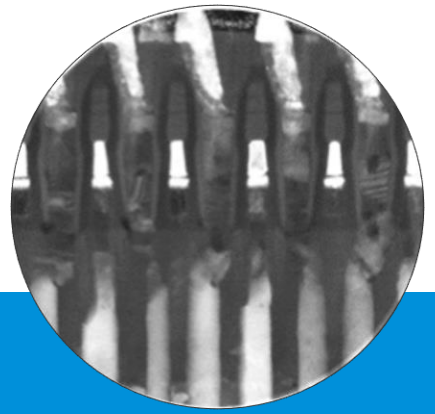
Continuing to Extend Roadmap for Cost and Performance Improvement



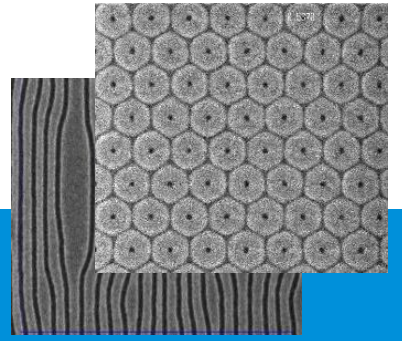
1Z Customer Qualification



1α Yield Improvement



1β Early Process Integration



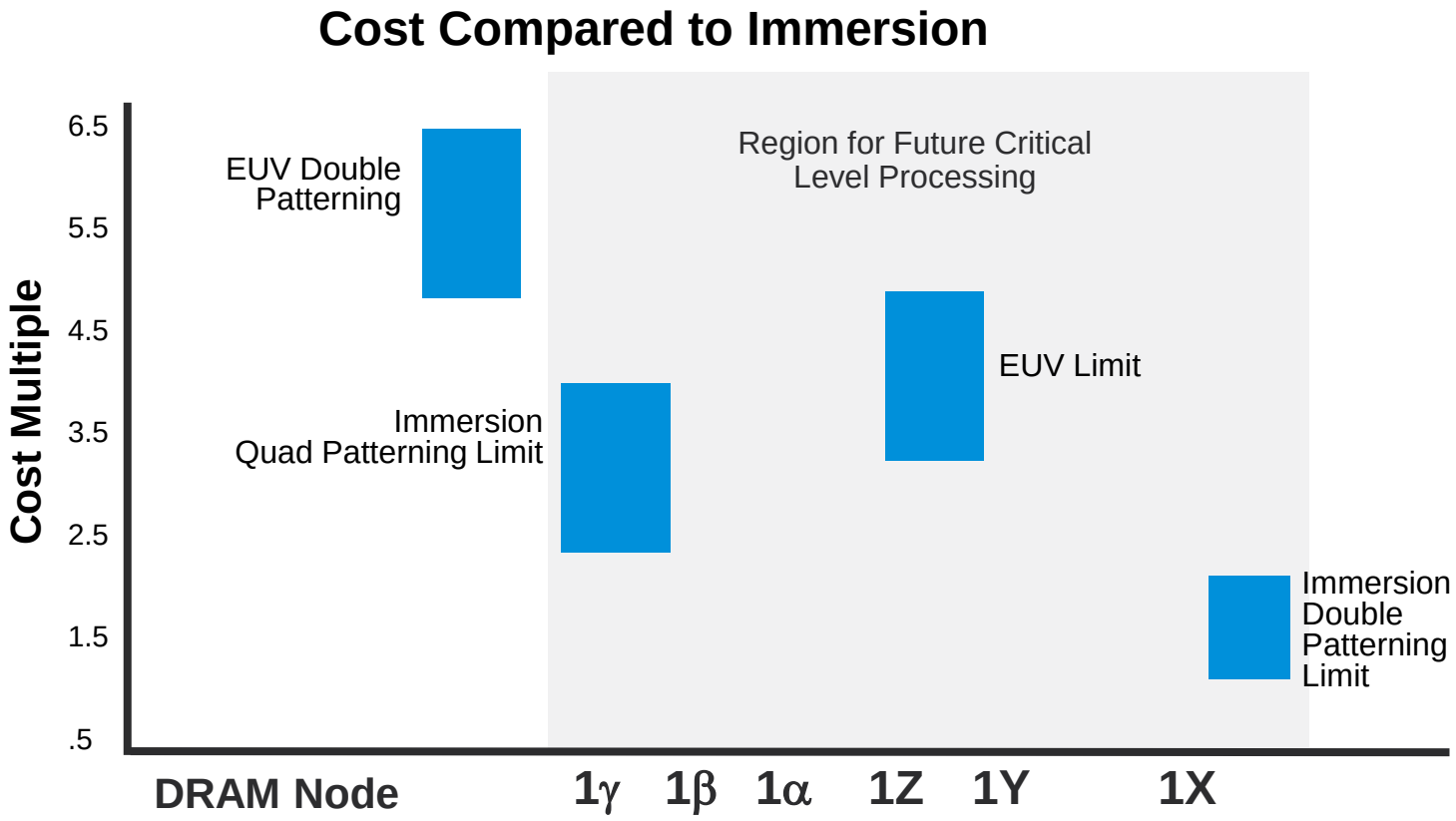
1γ Architectural Pathfinding

- Technology roadmap extending
- Difficult physics and cost challenges beyond **1β**
- Node transition value evolution

Optimized Approach to Lithography

Multiple Patterning Technology Optimized for Micron Future DRAM Nodes

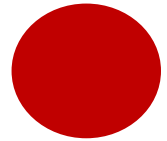
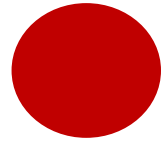
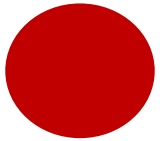
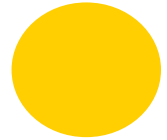
- Micron's pattern multiplication technology is a strategic advantage
- Proven technology capability and cost efficiency for 1Znm through 1γnm
- Ongoing evaluation of EUV Lithography for DRAM
- Prepared for implementation of EUV when beneficial to Micron



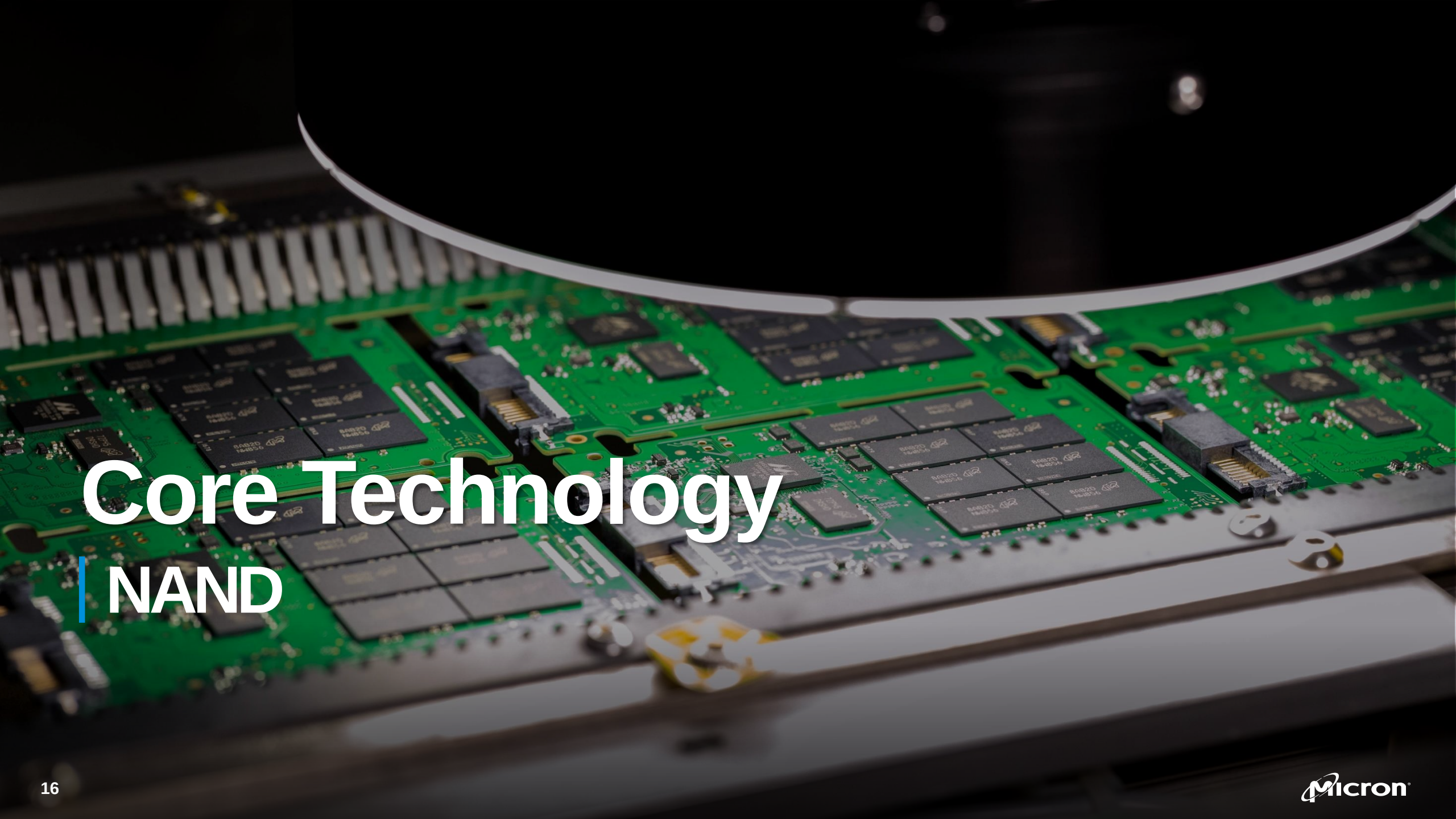
Lithography technology breakpoints & relative costs

Optimized Approach to Lithography

EUV Patterning Challenges for Advanced DRAM Applications

		Uniformity (Local Variation)	Cost Competitiveness ($ per Wafer)
DRAM 1Znm → 1αnm	**Immersion** Multi Patterning		
	EUV Single Exposure ***Optimal Dose***		
DRAM beyond 1αnm	**Immersion** Multi Patterning		
	EUV Single Exposure ***High Dose***		
	EUV Single Exposure ***Low Dose***		

Source: Micron



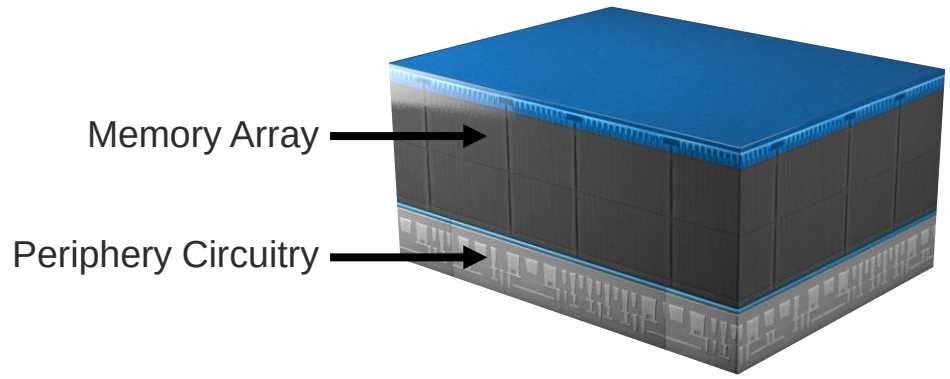
Core Technology

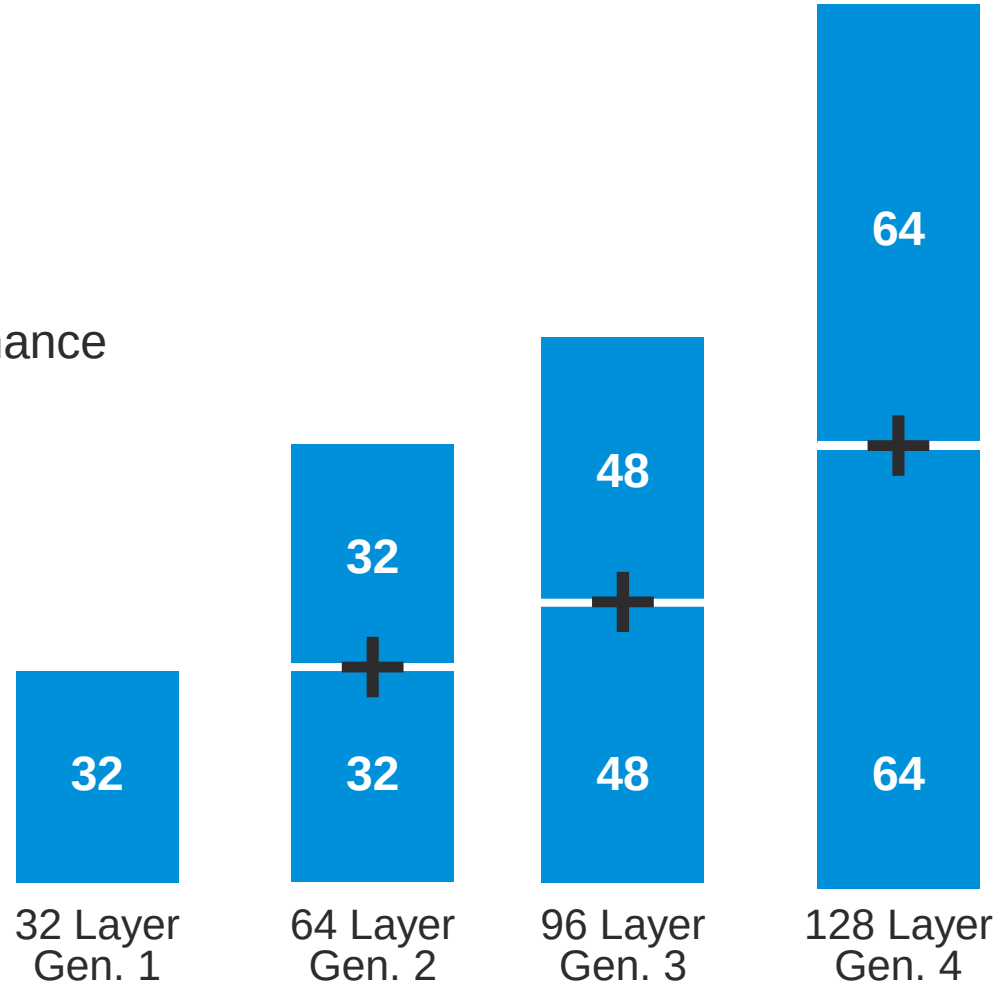
NAND

128 Layer NAND

Solid Progress on Replacement Gate Technology Provides Confidence for Transition

- Transition from Floating Gate to Replacement Gate
- Continued use of CMOS under array technology
- 3rd node of array stacking
- Enables leadership in die size, sequential write performance and write energy/bit

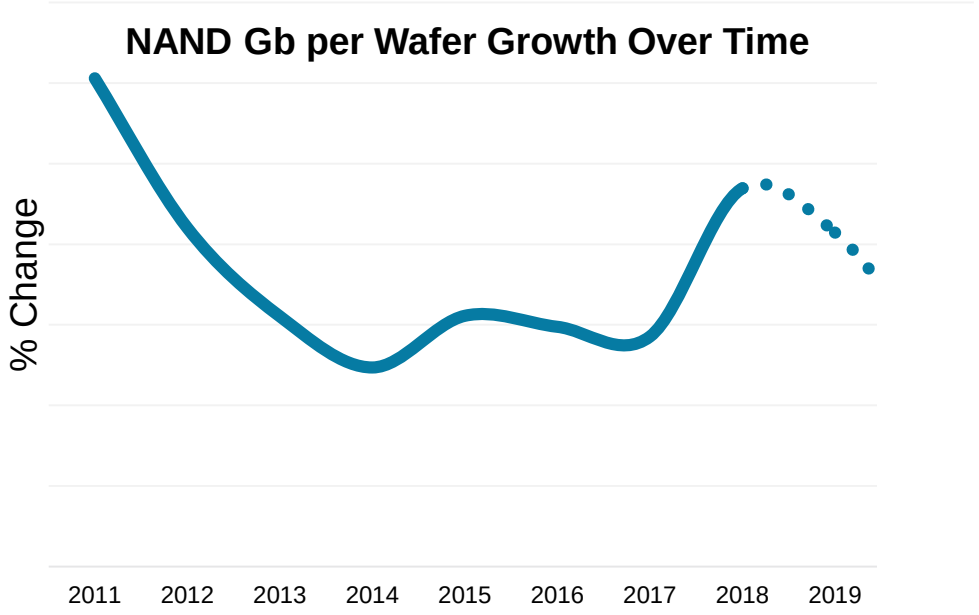


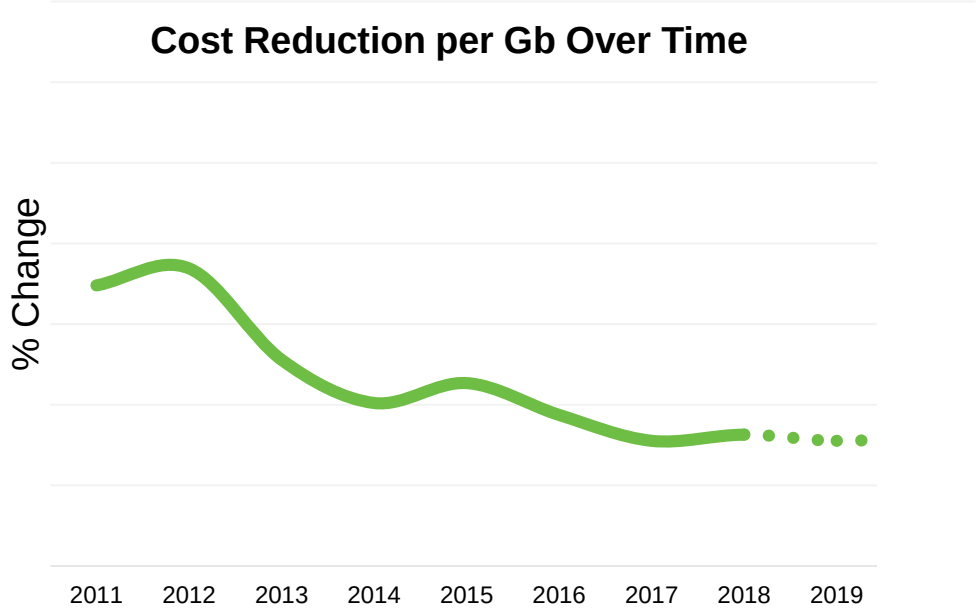


NAND Scaling Trends

Node to Node Benefits Reducing Post 3D NAND Transition

- Substantial increase in Gb/wafer driven by planar to 3D conversion
- Gb/wafer growth slows beyond the 64 layer transition
- Industry rate of cost reduction leveling off

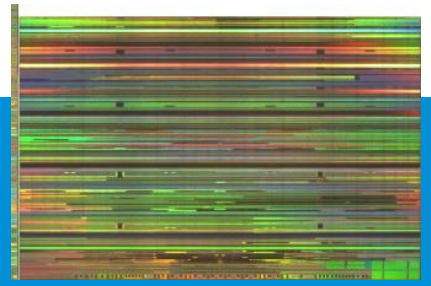




Source: Micron

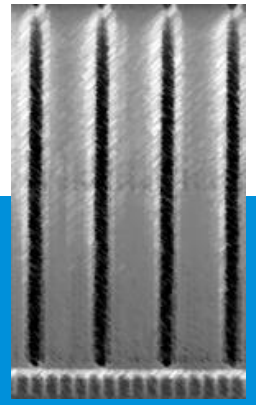
NAND Scaling: Leadership Through Technology Transition

Delivering World Leading Cost and Performance

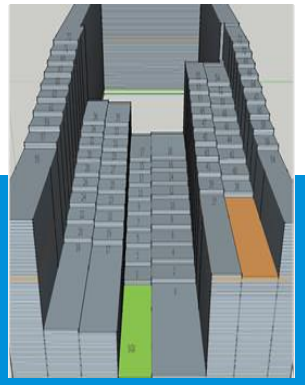


96 Layer FG
Mature Yield

128 Layer RG
Yield Improvement



1YY Layer RG
Early Process Integration



2XX Layer RG
Architectural Pathfinding

- RG technology transition primary focus
- Density increases and cost reductions slowing
- Driving towards cost and performance leadership

Team

Core Technology

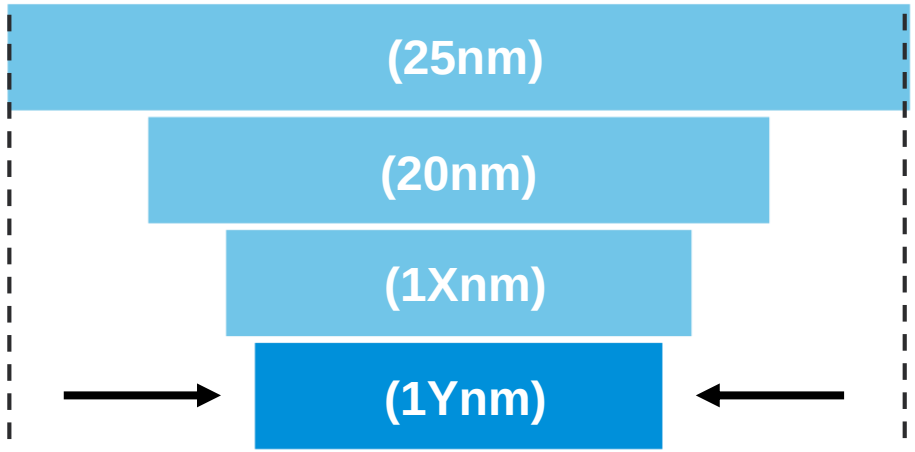
Execution

Delivering Faster Yield Ramps

Time to Mature Yield Reduced by More than Half

DRAM

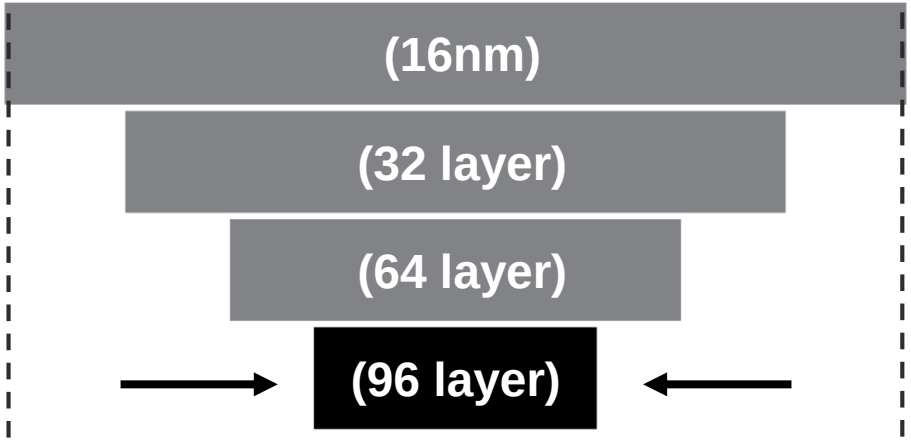
Time to Mature Yield Reduced by >50%



Time to Mature Yield

NAND

Time to Mature Yield Reduced by > 65%



Time to Mature Yield

Source: Micron

Driving our performance to a still higher level.

Team

Technology

Execution


Micron®